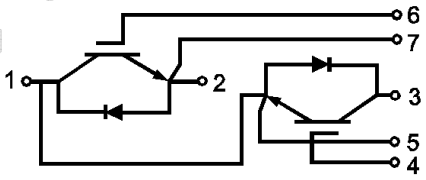
SILVERMICRO

GF150HF120T2VHE

IGBT Module

Features：

- Short Circuit Rated>10μs
- Low Saturation Voltage: $V_{CE\ (sat)}$ = 3.20V @ I_C = 150A , T_C=25℃
- Low Switching Loss
- 100% RBSOA Tested（2×Ic）
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



Applications：

- Welding Machine/ Cutting Machine
- Induction Heating
- Ultrasonic Device

Maximum Rated Values of IGBT(T_C=25℃ unless otherwise specified)

V_{CES}	Collector-Emitter Blocking Voltage		1200	V
V_{GES}	Gate-Emitter Voltage		±20	V
I_C	Continuous Collector Current	T_C = 80℃,	150	A
		T_C = 25℃	180	A
I_{CM}	Repetitive Peak Collector Current	T_J = 150℃	300	A
t_{SC}	Short Circuit Withstand Time		>10	μs
P_D	Maximum Power Dissipation per IGBT	T_C = 25℃ T_{Jmax}=150℃	1100	W

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Electrical Characteristics of IGBT (T_C=25℃ unless otherwise specified)

Static characteristics

Symbol	Description	Conditions		Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	IC = 3mA, VCE = VGE		4.5	5.2	5.5	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 150A, V_{GE} = 15V	T_J = 25℃		3.20	3.50	V
			T_J = 125℃		3.90		V
I_{CES}	Collector-Emitter Leakage Current	V_{GE} = 0V, V_{CE} = V_{CES}, T_J = 25℃				1	mA
I_{GES}	Gate-Emitter Leakage Current	V_{GE} = ±20V, V_{CE} = 0V, T_J = 25℃				400	nA
C_{ies}	Input Capacitance	V_{CE} = 25V, V_{GE} = 0V , f =1MHz			18.0		nF
C_{oes}	Output Capacitance				1.63		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	V_{CC} = 600V,I_C =150A, R_g= 6.2Ω,V_{GE} = ±15V, Inductive Load	T_J = 25℃		193		ns
			T_J = 125℃		185		
t_r	Rise Time		T_J = 25℃		127		ns
			T_J = 125℃		120		
$t_{d(off)}$	Turn-off Delay Time		T_J = 25℃		485		ns
			T_J = 125℃		512		
t_f	Fall Time		T_J = 25℃		127		ns
			T_J = 125℃		150		
E_{on}	Turn-on Switching Loss		T_J = 25℃		7.2		mJ
			T_J = 125℃		9.7		
E_{off}	Turn-off Switching Loss		T_J = 25℃		6.0		mJ
			T_J = 125℃		8.7		
Q_g	Total Gate Charge		T_J = 25℃		1890		nC
RBSOA	Reverse Bias Safe Operation Area	I_C=300A,V_{CC}=1050V,Vp=1200V, Rg = 6.2Ω, V_{GE}=+15V to 0V, T_J =150°C		Trapezoid			
SCSOA	Short Circuit Safe Operation Area	V_{CC} = 600V, V_{GE} = 15V, T_J = 150℃		10			μs
$R_{\theta JC}$	IGBT Thermal Resistance: Junction-To-Case				0.11		℃/W

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Maximum Rated Values of Diode (T_C=25℃ unless otherwise specified)

V_{RRM}	Repetitive Peak Reverse Voltage	1200	V
I_F	Diode Continuous Forward Current	150	A
I_{FM}	Diode Maximum Forward Current	300	A

Electrical Characteristics of Diode (T_C=25℃ unless otherwise specified)

Symbol	Description	Conditions		Min	Typ	Max	Unit
V_{FM}	Forward Voltage	I_F = 150A , V_{GE} = 0V	T_J = 25℃		2.2		V
			T_J = 125℃		2.4		
trr	Reverse Recovery Time	I_F＝150A, di/dt =1370A/μs, V_{rr} = 600V, V_{GE} = -15V	T_J = 25℃		155		ns
			T_J = 125℃		265		
I_{rr}	Peak Reverse Recovery Current		T_J = 25℃		95		A
			T_J = 125℃		118		
Q_{rr}	Reverse Recovery Charge		T_J = 25℃		9.4		μC
			T_J = 125℃		15.8		
E_{rec}	Reverse Recovery Energy		T_J = 25℃		3.6		mJ
			T_J = 125℃		6.9		
$R_{\theta JC}$	Diode Thermal Resistance: Junction-To-Case				0.21		℃/W

Module

Symbol	Description		Min	Typ	Max	Unit
V_{iso}	Isolation Voltage(All Terminals Shorted)	f = 50Hz, 1minute	2500			V
T_J	Maximum Junction Temperature				150	℃
T_{JOP}	Maximum Operating Junction Temperature Range		-40		+150	℃
T_{stg}	Storage Temperature		-40		+125	℃
$R_{\theta CS}$	Case-To-Sink (Conductive Grease Applied)			0.03		℃/W
T	Power Terminals Screw:M6		3.0		5.0	N·m
T	Mounting Screw:M6		4.0		6.0	N·m
G	Weight			300		g

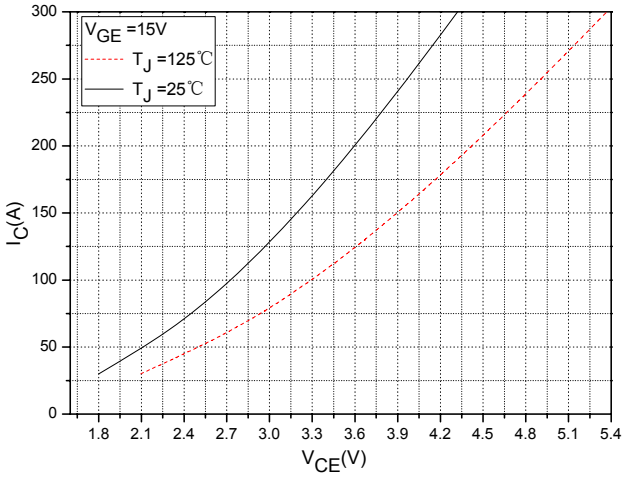


Fig.1 Typical Saturation Voltage Characteristics

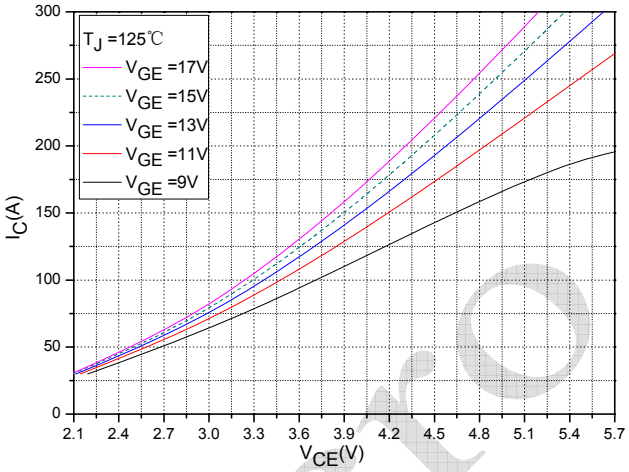


Fig.2 Typical Output Characteristics

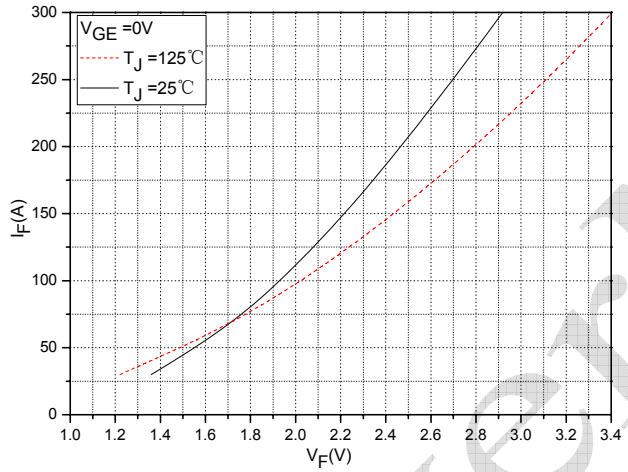


Fig.3 Forward Characteristics of Diode

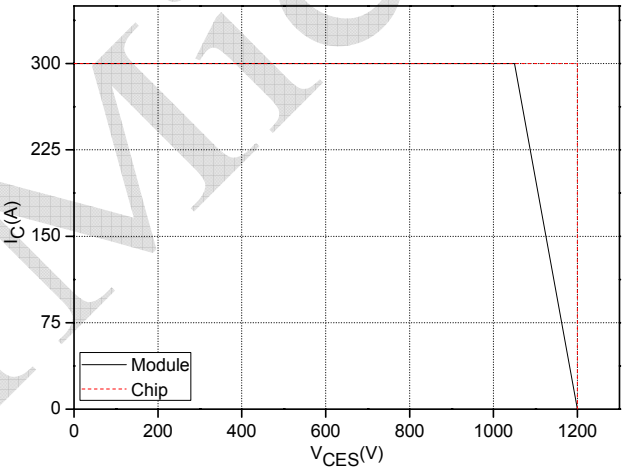


Fig.4 Reverse Bias Safe Operation Area (RBSOA)

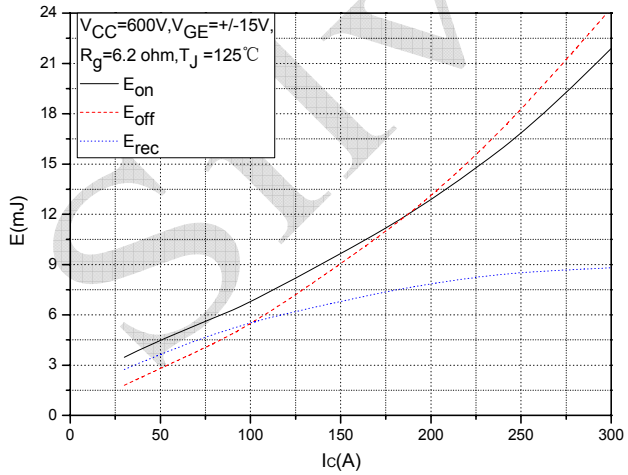


Fig.5 Typical Switching Loss vs. Collector Current

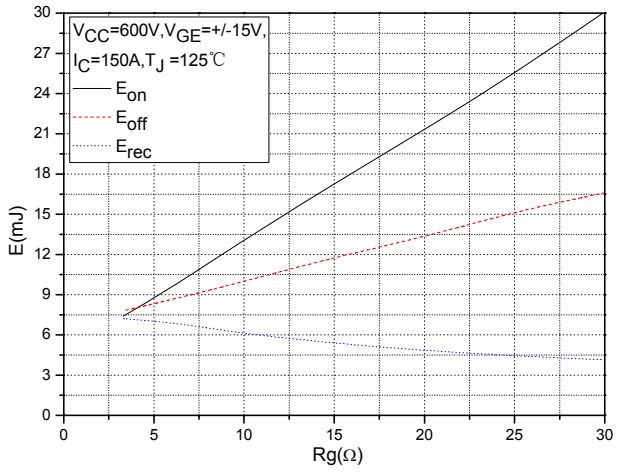


Fig.6 Typical Switching Loss vs. Gate Resistance

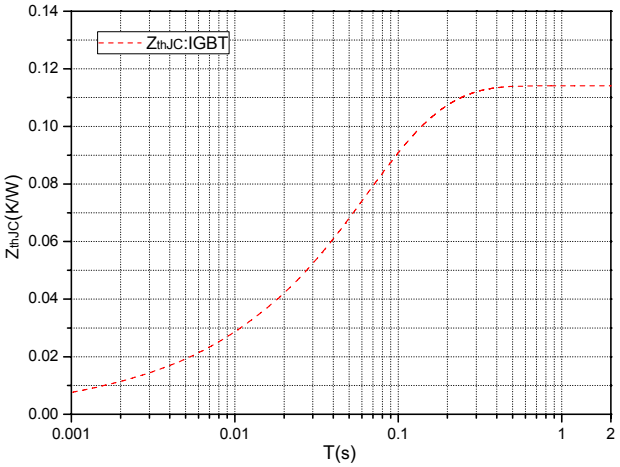


Fig.7 Transient thermal impedance (IGBT)

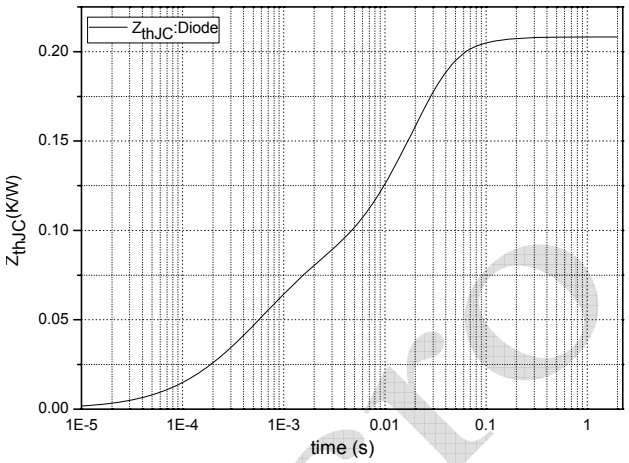


Fig.8 Transient thermal impedance (Diode)

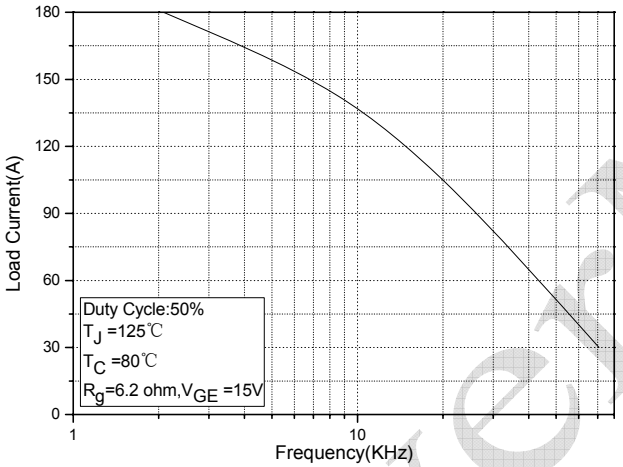


Fig.9 Typical Load Current vs. Frequency

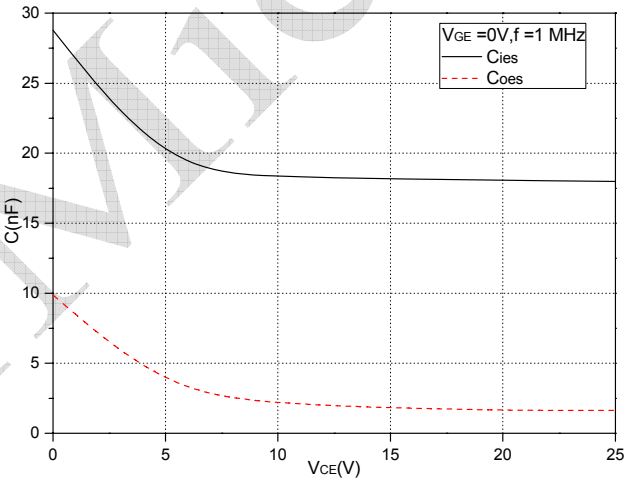
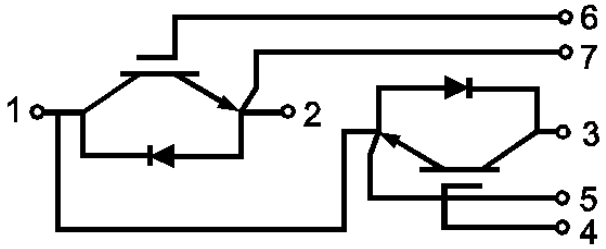
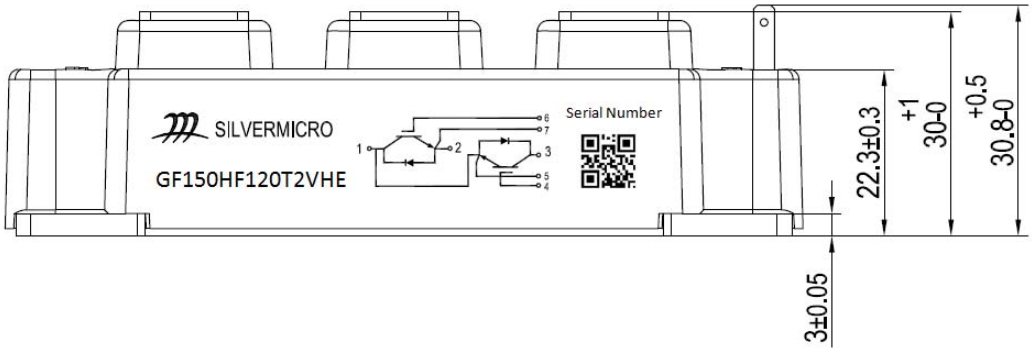


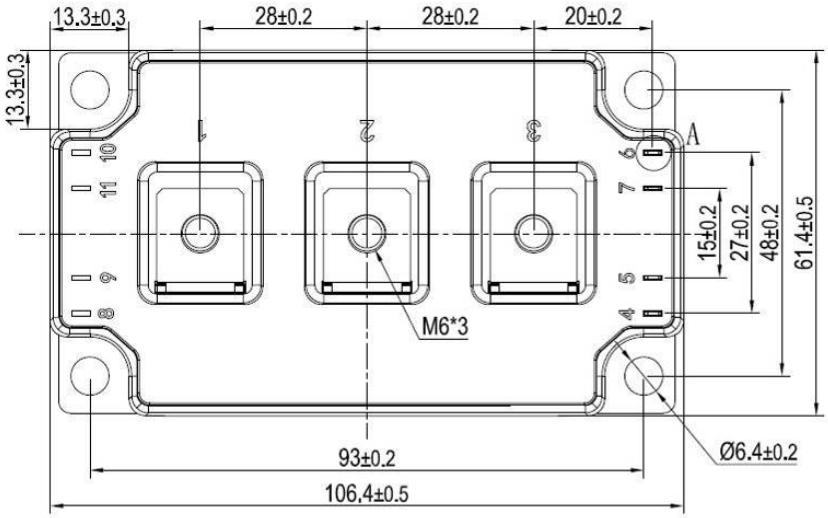
Fig.10 Capacitance Characteristics

Internal Circuit



Package Outline (Unit: mm):





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